**TOSHIBA** TD62M3701F

TOSHIBA BIPOLAR DIGITAL INTEGRATED CIRCUIT MULTI CHIP

# TD62M3701F

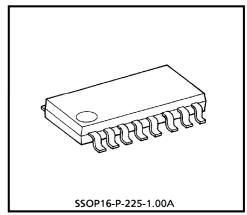
# LOW SATURATION VOLTAGE DRIVER FOR MOTOR

TD62M3701F is Multi Chip IC incorporates 6 low saturation discrete transistors which equipped bias resistor and fly-wheel diode.

This IC is suitable for a battery use motor drive applications.

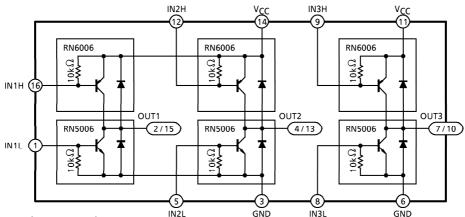
### **FEATURES**

- Suitable for high efficiency motor drive circuit
- Built-in fly-wheel diode
- Built-in bias resistor :  $R = 10k\Omega$  (Typ.)
- SSOP16 1mm pitch small package sealed
- Low saturation voltage
  - :  $V_{CE (sat)} = 0.29V (Typ.)$  at  $I_{O} = 1A$  $V_{CE (sat)} = 0.53V (Typ.)$  at  $I_{O} = 2A$ (Upper and lower side total)

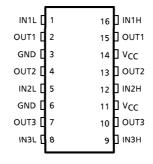


Weight: 0.14g (Typ.)

### **BLOCK DIAGRAM**



### PIN CONNECTION (TOP VIEW)



961001EBA2

TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

**TOSHIBA** 

### **MAXIMUM RATINGS** (Ta = 25°C)

| CHARACTERISTIC        | SYMBOL           | RATING              | UNIT |  |
|-----------------------|------------------|---------------------|------|--|
| Supply Voltage        | V <sub>CC</sub>  | 10                  | V    |  |
|                       | V <sub>CBO</sub> | V <sub>CBO</sub> 10 |      |  |
| Breakdown Voltage     | VCEO             | 10                  | V    |  |
|                       | V <sub>EBO</sub> | 6                   |      |  |
| Output Current        | lo               | 2                   | ^    |  |
| Catput Carrent        | IO (PEAK)        | 4 (Note 1)          | Α    |  |
| Base Current          | IB               | ± 0.4               | Α    |  |
| Base Current          | IB (PEAK)        | ±0.8 (Note 1)       |      |  |
| Diode Forward Current | lF               | 2 (Note 2)          | Α    |  |
| Power Dissipation     | PD               | 490                 | mW   |  |
| Junction Temperature  | Tj               | 150                 | °C   |  |
| Operating Temperature | T <sub>opr</sub> | - 40~85             | °C   |  |
| Storage Temperature   | T <sub>stg</sub> | <b>- 55∼150</b>     | °C   |  |

(Note 1) T = 10ms Max. and maximum duty is less than 30%.

(Note 2) T = 10ms single pulse

# **ELECTRICAL CHARACTERISTICS** (Ta = 25°C)

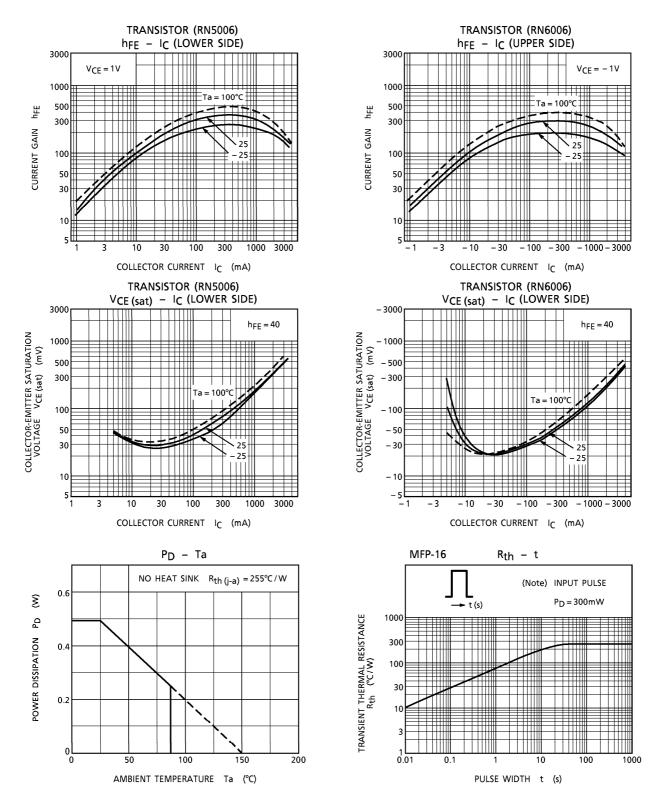
| CHARACTERISTIC        |            | SYMBOL                | TEST<br>CIR-<br>CUIT | TEST CONDITION                             | MIN. | TYP.   | MAX.   | UNIT |
|-----------------------|------------|-----------------------|----------------------|--|------|--------|--------|------|
| Current Gain          |            | h <sub>FE</sub> (1)   | _                    | $V_{CE} = 1V, I_{C} = 0.5A$                | 160  | _      | 600    | _    |
|                       |            | h <sub>FE</sub> (2)   | _                    | $V_{CE} = 1V, I_{C} = 2.0A$                | 60   | 130    |        |      |
| Saturation<br>Voltage | Upper Side | VCE (sat)             | _                    | $I_C = -1A$ , $I_B = -25mA$                | _    | - 0.16 | - 0.22 |      |
|                       |            |                       |                      | $I_C = -2A$ , $I_B = -50mA$                | _    | -0.28  | - 0.45 |      |
|                       | Lower Side |                       |                      | I <sub>C</sub> = 1A, I <sub>B</sub> = 25mA | _    | 0.13   | 0.22   |      |
|                       |            |                       |                      | I <sub>C</sub> = 2A, I <sub>B</sub> = 50mA | _    | 0.25   | 0.45   |      |
|                       | Summing    |                       |                      | I <sub>C</sub> = 1A, I <sub>B</sub> = 25mA | _    | 0.29   | 0.42   |      |
|                       | Total      |                       |                      | I <sub>C</sub> = 2A, I <sub>B</sub> = 50mA | _    | 0.53   | 0.85   |      |
| Transition Frequency  |            | f <sub>T</sub>        | _                    | $V_{CE} = 2V, I_{C} = 0.5A$                | _    | 150    | _      | MHz  |
| Leakage               | Upper Side | lOL                   |                      | V <sub>CC</sub> = -10V                     | _    | 0      | - 5    | μΑ   |
| Current               | Lower Side |                       | -                    | V <sub>CC</sub> = 10V                      | _    | 0      | 5      |      |
| Forward               | Upper Side | V <sub>F</sub>        | _                    | I <sub>F</sub> = 300mA                     | _    | 0.89   | 1.2    | V    |
|                       |            |                       |                      | I <sub>F</sub> = 450mA 10ms pulse          | _    | 1.60   | _      |      |
|                       | Lower Side |                       |                      | I <sub>F</sub> = 300mA                     | _    | 0.89   | 1.2    |      |
|                       |            |                       |                      | I <sub>F</sub> = 450mA 10ms pulse          | _    | 1.60   | _      |      |
| Base-Emitte           | r Resistor | R <sub>BE</sub>       |                      | _  | 7    | 10     | 13     | kΩ   |
| Base-Emitter Forward  |            | VBE (PNP)             | _                    | $V_{CE} = -1V$ , $I_{C} = -2A$             | _    | - 0.84 | - 1.5  | V    |
| Voltage               |            | V <sub>BE</sub> (NPN) |                      | V <sub>CE</sub> = 1V, I <sub>C</sub> = 2A  |      | 0.84   | 1.5    | , v  |

961001EBA2'

The products described in this document are subject to foreign exchange and foreign trade control laws.

The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.

The information contained herein is subject to change without notice.



## PRECAUTIONS for USING

Utmost care is necessary in the design of the output line, V<sub>CC</sub> and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

# OUTLINE DRAWING SSOP16-P-225-1.00A Unit : mm 0.6TYP 8.7MAX 8.2±0.2 0.525±0.2

Weight: 0.14g (Typ.)